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**TRANSMITTAL
FORM**

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Total Number of Pages in This Submission

Application Number 10/822,118

Filing Date April 8, 2004

First Named Inventor Gurtej S. Sandhu

Art Unit 2812

Examiner Name Unknown

Attorney Docket Number MI22-2268

ENCLOSURES (Check all that apply)☐ Fee Transmittal Form☐ Fee Attached☐ Amendment/Reply☐ After Final☐ Affidavits/declaration(s)☐ Extension of Time Request☐ Express Abandonment Request☒ Supplemental
Information Disclosure Statement☐ Certified Copy of Priority
Document(s)☐ Reply to Missing Parts/
Incomplete Application☐ Reply to Missing Parts
under 37 CFR 1.52 or 1.53☐ Drawing(s)☐ Licensing-related Papers☐ Petition☐ Petition to Convert to a
Provisional Application☐ Power of Attorney, Revocation☐ Change of Correspondence Address☐ Terminal Disclaimer☐ Request for Refund☐ CD, Number of CD(s) _____☐ Landscape Table on CD☐ After Allowance Communication to TC☐ Appeal Communication to Board
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Mark S. Matkin

Date

10/25/04

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32,268

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EV372470015



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. 10/822,118
Filing Date April 8, 2004
Inventor Gurtej S. Sandhu et al.
Assignee Micron Technology, Inc.
Group Art Unit 2812
Examiner Unknown
Attorney Docket No. MI22-2268
Customer No. 021567
Title: Methods of Forming a Reaction Product and Methods of Forming a
Conductive Metal Silicide by Reaction of Metal with Silicon

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached PTO-1449 form is submitted in compliance with 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S. patents or U.S. patent application publications are included, as the date of filing of this patent application occurs after June 30, 2003. Copies of all other references are attached. No admission is made regarding whether all the listed references are prior art.

Citation of the referenced art is respectfully requested.

This Supplemental Information Disclosure Statement is being filed before the mailing date of a first Office Action. There, no fee is believed to be required.

However, in the event that a fee is required for this filing, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 10-25-04

By: 
Mark S. Matkin
Reg. No. 32,268

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		ATTY. DOCKET NO. MI22-2268		SERIAL NO. 10/822,118	
		APPLICANT: Gurtej S. Sandhu et al.			
		FILING DATE April 8, 2004		GROUP 2812	

U.S. PATENT DOCUMENTS							
*Examiner's Initials	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA	3,349,474	12/1963	D. H. Rauscher				
AB	5,904,517	05/1999	Gardner et al.	438	197		
AC	5,998,264	12/1999	Wu	438	260		
AD	6,180,465 B1	01/2001	Gardner et al.	438	291		
AE	6,207,485 B1	03/2001	Gardner et al.	438	216		
AF	6,548,854 B1	04/2003	Kizilyalli et al.	257	310		
AG							
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AI	2003/0045078 A1	03/2003	Ahn et al.	438	585		

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AJ	EP 0 851 473 A2	01/1998	EPO			X	
AK							
AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
AM		Chang et al., Silicon surface treatments in advanced MOS gate processing, Microelectronic Engineering, (2004), pages 130-135	
AN		Lemberger et al., Electrical characterization and reliability aspects of zirconium silicate films obtained from novel MOCVD precursors, Microelectronic Engineering (2004), pages 315-320	
AO		Lu et al., Effects of the TaN _x interface layer on doped tantalum oxide high-k films, VACUUM (2004), pages 1-9	
EXAMINER		DATE CONSIDERED	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
AM		Robertson et al., Atomic structure, band offsets, growth and defects at high-K oxide:Si interfaces, Microelectronic Engineering (2004) pages 112-120	
AN		Singh et al., High and Low Dielectric Constant Materials, The Electrochemical Society <i>Interface</i> , Summer 1999, pages 26-30	
AO			
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